8-Bit Addressable Latch 1-of-8 Decoder

High-Performance Silicon-Gate CMOS

The MC74HC259A is identical in pinout to the LS259. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

The HC259A has four modes of operation as shown in the mode selection table. In the addressable latch mode, the data on Data In is written into the addressed latch. The addressed latch follows the data input with all non-addressed latches remaining in their previous states. In the memory mode, all latches remain in their previous state and are unaffected by the Data or Address inputs. In the one-of-eight decoding or demultiplexing mode, the addressed output follows the state of Data In with all other outputs in the LOW state. In the Reset mode all outputs are LOW and unaffected by the address and data inputs. When operating the HC259A as an addressable latch, changing more than one bit of the address could impose a transient wrong address. Therefore, this should only be done while in the memory mode.

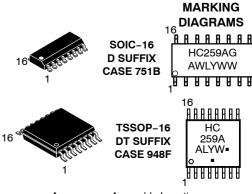
Features

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2 to 6 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant



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A = Assembly Location

WL, L = Wafer Lot YY, Y = Year WW, W = Work Week G or • = Pb-Free Package

(Note: Microdot may be in either location)

PIN ASSIGNMENT

A0 [1 ●	16] v _{cc}
A1 [2	15] RESET
A2 [3	14] ENABLE
Q0 [4	13] data in
Q1 [5	12] Q7
Q2 [6	11] Q6
Q3 [7	10] Q5
GND [8	9] Q4

MODE SELECTION TABLE

Enable	Reset	Mode
L	Н	Addressable Latch
H	Н	Memory
L	L	8-Line Demultiplexer
Н	L	Reset

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

4 Q0 **ADDRESS INPUTS** 6 Q2 7 Q3 **NONINVERTING** 9 Q4 **OUTPUTS** 10 Q5 DATA IN 13 11 Q6 12 Q7 RESET PIN 16 = V_{CC} ENABLE 14 PIN 8 = GND

Figure 1. Logic Diagram

LATCH SELECTION TABLE

Ad	dress Inp	uts	
A ₂	A ₁	A ₀	Latch Addressed
L	L	L	Q0
L	L	Н	Q1
L	Н	L	Q2
L	Н	Н	Q3
Н	L	L	Q4
Н	L	Н	Q5
Н	Н	L	Q6
Н	Н	Н	Q7

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	-0.5 to +7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	-0.5 to V _{CC} + 0.5	٧
V _{out}	DC Output Voltage (Referenced to GND)	-0.5 to V _{CC} + 0.5	٧
I _{in}	DC Input Current, per Pin	±20	mA
l _{out}	DC Output Current, per Pin	±25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	±50	mA
P _D	Power Dissipation in Still Air, SOIC Package TSSOP Package	500 450	mW
T _{stg}	Storage Temperature	-65 to + 150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	2.0	6.0	V	
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Reference	d to GND)	0	V_{CC}	٧
T _A	Operating Temperature, All Package Types	-55	+125	°C	
t _r , t _f	(Figure 2) V	CC = 2.0 V CC = 3.0 V CC = 4.5 V CC = 6.0 V	0 0 0 0	1000 600 500 400	ns

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gu	aranteed Li	mit	
Symbol	Parameter	Test Conditions	V _{CC} V	– 55 to 25°C	≤ 85 °C	≤ 125°C	Unit
V _{IH}	Minimum High-Level Input Voltage	V_{out} = 0.1 V or V_{CC} - 0.1 V $ I_{out} \le 20 \mu A$	2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	V
V _{IL}	Maximum Low-Level Input Voltage	V_{out} = 0.1 V or V_{CC} – 0.1 V $ I_{out} \le 20 \mu A$	2.0 3.0 4.5 6.0	0.5 0.9 1.35 1.80	0.5 0.9 1.35 1.80	0.5 0.9 1.35 1.80	V
V _{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \mu\text{A}$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$ \begin{aligned} V_{in} = V_{IH} \text{ or } V_{IL} & & I_{out} \leq 2.4 \text{ mA} \\ & & I_{out} \leq 4.0 \text{ mA} \\ & & I_{out} \leq 5.2 \text{ mA} \end{aligned} $	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.20 3.70 5.20	
V _{OL}	Maximum Low-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \mu\text{A}$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$\label{eq:Vin} \begin{aligned} V_{in} = V_{IH} \text{ or } V_{IL} & & I_{out} \leq 2.4 \text{ mA} \\ & & I_{out} \leq 4.0 \text{ mA} \\ & & I_{out} \leq 5.2 \text{ mA} \end{aligned}$	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.40 0.40 0.40	
l _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	6.0	± 0.1	± 1.0	± 1.0	μΑ
I _{CC}	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	6.0	4	40	160	μΑ

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input $t_{\rm f}$ = $t_{\rm f}$ = 6 ns)

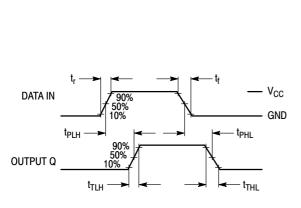
			Gu			
Symbol	Parameter	V _{CC} V	– 55 to 25°C	≤ 85 °C	≤ 125°C	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Data to Output (Figures 2 and 7)	2.0 3.0 4.5 6.0	125 45 32 25	160 60 32 28	175 70 42 33	ns
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Address Select to Output (Figures 3 and 7)	2.0 3.0 4.5 6.0	150 60 32 28	175 70 40 30	200 80 45 35	ns
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Enable to Output (Figures 4 and 7)	2.0 3.0 4.5 6.0	150 60 32 28	175 70 40 30	200 80 45 35	ns
t _{PHL}	Maximum Propagation Delay, Reset to Output (Figures 5 and 7)	2.0 3.0 4.5 6.0	110 36 22 19	125 45 26 23	160 60 32 28	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 2 and 7)	2.0 3.0 4.5 6.0	75 27 15 13	95 32 19 16	110 36 22 19	ns
C _{in}	Maximum Input Capacitance	-	10	10	10	pF

		Typical @ 25°C, V _{CC} = 5.0 V	
C _{PD}	Power Dissipation Capacitance (Per Package)	30	pF

TIMING REQUIREMENTS (Input $t_r = t_f = 6 \text{ ns}$)

			Gu	aranteed Li	mit	
Symbol	Parameter	V _{CC}	– 55 to 25°C	≤ 85 °C	≤ 125°C	Unit
t _{su}	Minimum Setup Time, Address or Data to Enable (Figure 6)	2.0 3.0 4.5 6.0	75 30 15 13	95 40 19 16	110 55 22 19	ns
t _h	Minimum Hold Time, Enable to Address or Data (Figure 6)	2.0 3.0 4.5 6.0	1 1 1 1	1 1 1 1	1 1 1	ns
t _w	Minimum Pulse Width, Reset or Enable (Figure 4 or 5)	2.0 3.0 4.5 6.0	70 27 15 13	90 32 19 16	100 36 22 19	ns
t _r , t _f	Maximum Input Rise and Fall Times (Figure 2)	2.0 3.0 4.5 6.0	1000 800 500 400	1000 800 500 400	1000 800 500 400	ns

SWITCHING WAVEFORMS



DATA IN

- GND

VCC

- GND

VCC

- GND

- GND

- VCC

- GND

Figure 2.

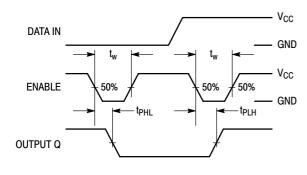
Figure 3.

- V_{CC}

- GND

 V_{CC}

- GND



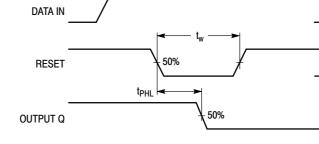
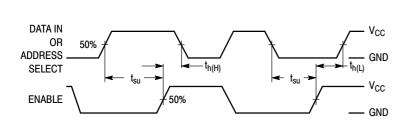
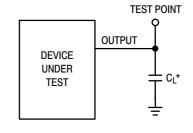


Figure 4.

Figure 5.





*Includes all probe and jig capacitance

Figure 6.

Figure 7. Test Circuit

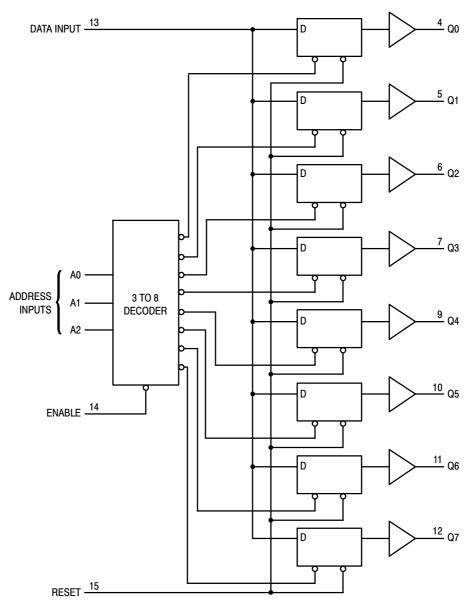


Figure 8. Expanded Logic Diagram

ORDERING INFORMATION

Device	Package	Shipping [†]	
MC74HC259ADG	SOIC-16 (Pb-Free)	48 Units / Rail	
MC74HC259ADR2G	SOIC-16 (Pb-Free)	2500 / Tape & Reel	
MC74HC259ADTR2G	TSSOP-16 (Pb-Free)	2500 / Tape & Reel	
MC74HC259ADTG	TSSOP-16 (Pb-Free)	96 Units / Rail	
NLVHC259ADR2G*	SOIC-16 (Pb-Free)	2500 / Tape & Reel	

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

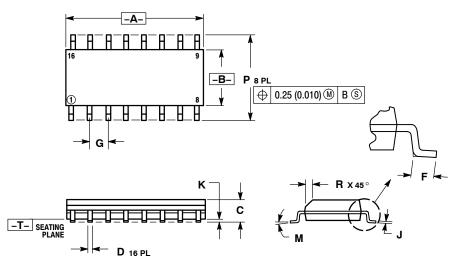
^{*}NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable





SOIC-16 CASE 751B-05 **ISSUE K**

DATE 29 DEC 2006



⊕ 0.25 (0.010) M T B S A S

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD ENGREPHING.

- PROTRUSION.

 MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR PROTRUSION.
 SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D
 DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	9.80	10.00	0.386	0.393	
В	3.80	4.00	0.150	0.157	
U	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050 BSC		
7	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	0°	7°	0°	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:		
	COLLECTOR	PIN 1.	CATHODE		COLLECTOR, DYE #1	PIN 1.	COLLECTOR, DYE #1	
2.	BASE	2.	ANODE	2.	BASE, #1	2.	COLLECTOR, #1	
3.	EMITTER	3.	NO CONNECTION	3.	EMITTER, #1	3.	COLLECTOR, #2	
4.	NO CONNECTION	4.	CATHODE	4.	COLLECTOR, #1	4.	COLLECTOR, #2	
5.	EMITTER	5.	CATHODE	5.	COLLECTOR, #2	5.	COLLECTOR, #3	
6.	BASE	6.	NO CONNECTION	6.	BASE, #2	6.	COLLECTOR, #3	
7.	COLLECTOR	7.		7.		7.	COLLECTOR, #4	
8.	COLLECTOR	8.	CATHODE	8.	COLLECTOR, #2	8.	COLLECTOR, #4	
9.	BASE	9.	CATHODE	9.	COLLECTOR, #3	9.	BASE, #4	
10.	EMITTER	10.	ANODE	10.		10.	EMITTER, #4	
11.	NO CONNECTION	11.	NO CONNECTION		EMITTER, #3	11.	BASE, #3	
12.	EMITTER		CATHODE		COLLECTOR, #3	12.		RECOMMENDED
13.	BASE	13.	CATHODE	13.		13.	BASE, #2	
14.	COLLECTOR	14.	NO CONNECTION	14.		14.	EMITTER, #2	SOLDERING FOOTPRINT*
15.	EMITTER	15.	ANODE			15.	BASE, #1	
16.	COLLECTOR	16.	CATHODE	16.	COLLECTOR, #4	16.	EMITTER, #1	8X
								← 6.40 →
STYLE 5:		STYLE 6:		STYLE 7:				10/110 -
PIN 1.	DRAIN, DYE #1		CATHODE	PIN 1.	SOURCE N-CH			16X 1.12
2.	DRAIN, #1	2.	CATHODE	2.	COMMON DRAIN (OUTPUT	Γ)		
3.	DRAIN, #2	3.	CATHODE	3.	COMMON DRAIN (OUTPUT	Γ)	1	1 16
4.	DRAIN, #2	4.	CATHODE	4.	GATE P-CH		<u> </u>	
5.	DRAIN, #3	5.	CATHODE	5.	COMMON DRAIN (OUTPUT		-	
6.	DRAIN, #3	6.	CATHODE	6.	COMMON DRAIN (OUTPUT		16X	_ _
7.	DRAIN, #4	7.		7.		7)	0.58 -	
8.	DRAIN, #4	8.	CATHODE	8.	SOURCE P-CH			
9.	GATE, #4	9.	ANODE	9.	SOURCE P-CH	_		
10.	SOURCE, #4	10.	ANODE	10.	COMMON DRAIN (OUTPUT		-	 -
11.	GATE, #3		ANODE	11.				
12.	SOURCE, #3		ANODE	12.)		_ _
13.	GATE, #2		ANODE	13.	GATE N-CH	-		
14.	SOURCE, #2		ANODE ANODE	14.				☐ PITCH
15.	GATE, #1	15.		15.	COMMON DRAIN (OUTPUT)		
16.	SOURCE, #1	16.	ANODE	16.	SOURCE N-CH			
								□8 9
								DIMENSIONS: MILLIMETERS

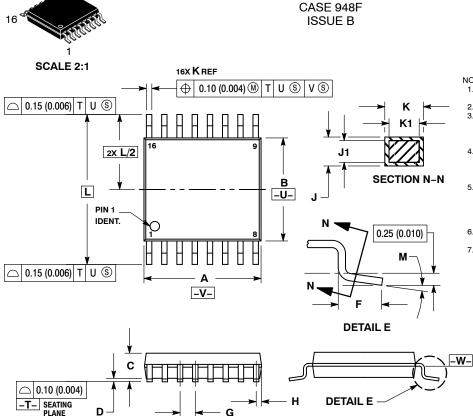
*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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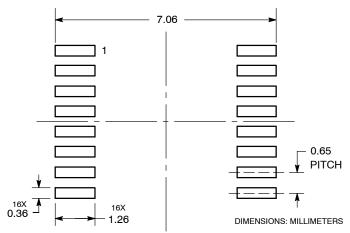
TSSOP-16 WB

NOTES

- DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT
- EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE
 INTERLEAD FLASH OR PROTRUSION.
- INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL
 NOT EXCEED 0.25 (0.010) PER SIDE.
 DIMENSION K DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABILE DAMBAR
 PROTRUSION SHALL BE 0.08 (0.003) TOTAL
 IN EXCESS OF THE K DIMENSION AT
 MAXIMUM MATERIAL CONDITION.
 TERMINIAL NILMBERS ADE SUCIUMI ECIP.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
М	0 °	8 °	0 °	8 °

RECOMMENDED SOLDERING FOOTPRINT*



^{*}For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



= Specific Device Code XXXX Α = Assembly Location

= Wafer Lot L = Year W = Work Week G or • = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present. Some products may not follow the Generic Marking.

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